TOSHIBA Field Effect Transistor Silicon P Channel MOS Type (U-MOSIII)

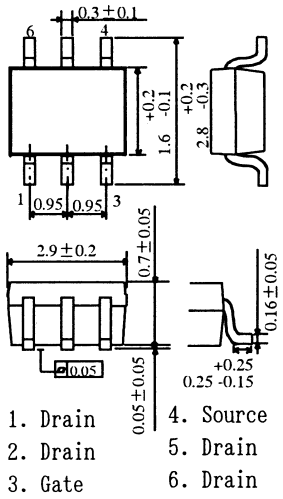
TPC6104

Notebook PC Applications

Portable Equipment Applications

- Low drain-source ON resistance: $R_{DS\ (ON)}$ = 33 mΩ (typ.)
- High forward transfer admittance: $|Y_{fs}|$ = 12 S (typ.)
- Low leakage current: I_{DSS} = −10 μA (max) (V_{DS} = −20 V)
- Enhancement mode: V_{th} = −0.5 to −1.2 V (V_{DS} = −10 V, I_D = −200 μA)

Unit: mm



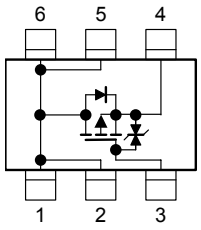
JEDEC	—
JEITA	—
TOSHIBA	2-3T1A

Weight: 0.011 g (typ.)

Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit
Drain-source voltage		V_{DSS}	−20	V
Drain-gate voltage (R_{GS} = 20 kΩ)		V_{DGR}	−20	V
Gate-source voltage		V_{GSS}	±8	V
Drain current	DC (Note 1)	I_D	−5.5	A
	Pulse (Note 1)	I_{DP}	−22	
Drain power dissipation	(t = 5 s) (Note 2a)	P_D	2.2	W
Drain power dissipation	(t = 5 s) (Note 2b)	P_D	0.7	W
Single pulse avalanche energy	(Note 3)	E_{AS}	4.9	mJ
Avalanche current		I_{AR}	−2.75	A
Repetitive avalanche energy	(Note 4)	E_{AR}	0.22	mJ
Channel temperature		T_{ch}	150	°C
Storage temperature range		T_{stg}	−55~150	°C

Circuit Configuration



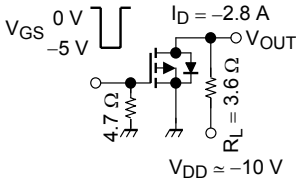
Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to ambient (t = 5 s) (Note 2a)	$R_{th\ (ch-a)}$	56.8	°C/W
Thermal resistance, channel to ambient (t = 5 s) (Note 2b)	$R_{th\ (ch-a)}$	178.5	°C/W

Note: Note 1, Note 2, Note 3, Note 4 and Note 5: See the next page.

This transistor is an electrostatic-sensitive device. Please handle with caution.

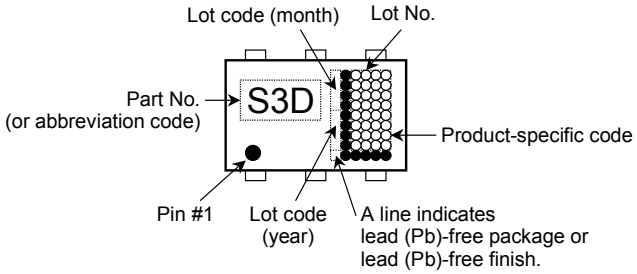
Electrical Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		I_{GSS}	V_{GS} = ±8 V, V_{DS} = 0 V	—	—	±10	μA
Drain cut-off current		I_{DSS}	V_{DS} = −20 V, V_{GS} = 0 V	—	—	−10	μA
Drain-source breakdown voltage		$V_{(BR)\ DSS}$	I_D = −10 mA, V_{GS} = 0 V	−20	—	—	V
		$V_{(BR)\ DSX}$	I_D = −10 mA, V_{GS} = 8 V	−12	—	—	
Gate threshold voltage		V_{th}	V_{DS} = −10 V, I_D = −200 μA	−0.5	—	−1.2	V
Drain-source ON resistance		$R_{DS\ (ON)}$	V_{GS} = −1.8 V, I_D = −1.4 A	—	78	120	mΩ
		$R_{DS\ (ON)}$	V_{GS} = −2.5 V, I_D = −2.8 A	—	49	60	
		$R_{DS\ (ON)}$	V_{GS} = −4.5 V, I_D = −2.8 A	—	33	40	
Forward transfer admittance		$\|Y_{fs}\|$	V_{DS} = −10 V, I_D = −2.8 A	6	12	—	S
Input capacitance		C_{iss}	V_{DS} = −10 V, V_{GS} = 0 V, f = 1 MHz	—	1430	—	pF
Reverse transfer capacitance		C_{rss}		—	200	—	
Output capacitance		C_{oss}		—	240	—	
Switching time	Rise time	t_r	 Duty ≦ 1%, t_w = 10 μs	—	8.5	—	ns
	Turn-on time	t_{on}		—	15	—	
	Fall time	t_f		—	20	—	
	Turn-off time	t_{off}		—	66	—	
Total gate charge (gate-source plus gate-drain)		Q_g	V_{DD} ≃ −16 V, V_{GS} = −5 V, I_D = −5.5 A	—	19	—	nC
Gate-source charge		Q_{gs}		—	14	—	
Gate-drain (“miller”) charge		Q_{gd}		—	5	—	

Source-Drain Ratings and Characteristics (Ta = 25°C)

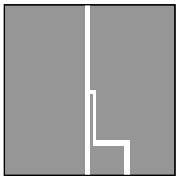
Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Drain reverse current	Pulse (Note 1)	I_{DRP}	—	—	—	−22	A
Forward voltage (diode)		V_{DSF}	I_{DR} = −5.5 A, V_{GS} = 0 V	—	—	1.2	V

Marking (Note 5)



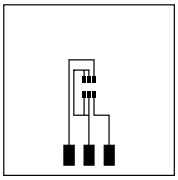
Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: (a) Device mounted on a glass-epoxy board (a) (t = 5 s)
(b) Device mounted on a glass-epoxy board (b) (t = 5 s)



FR-4
25.4 × 25.4 × 0.8
Unit: (mm)

(a)



FR-4
25.4 × 25.4 × 0.8
Unit: (mm)

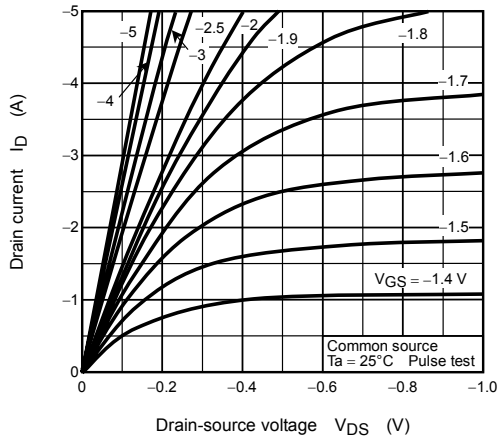
(b)

Note 3: V_{DD} = −16 V, T_{ch} = 25°C (initial), L = 0.5 mH, R_G = 25 Ω, I_{AR} = −2.75 A

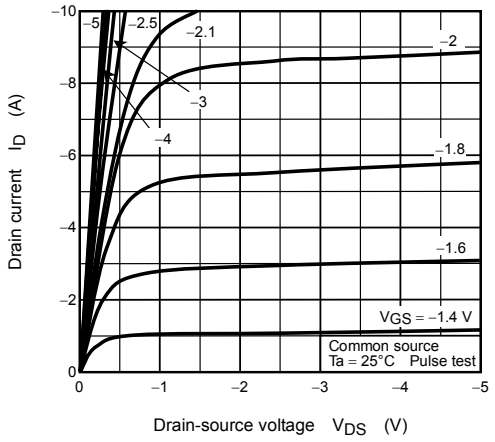
Note 4: Repetitive rating;:pulse width limited by maximum channel temperature

Note 5: • on lower left of the marking indicates Pin 1.

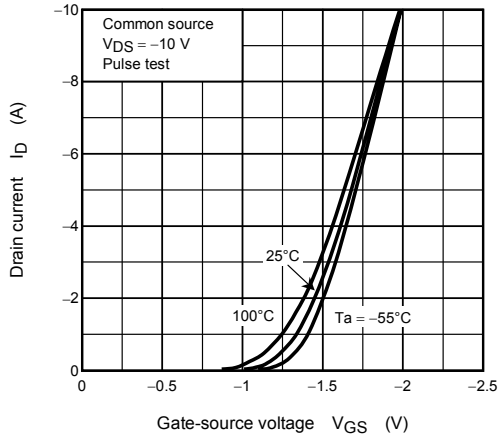
$I_D - V_{DS}$



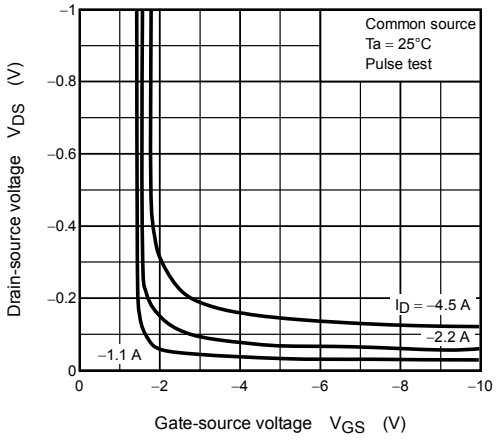
$I_D - V_{DS}$



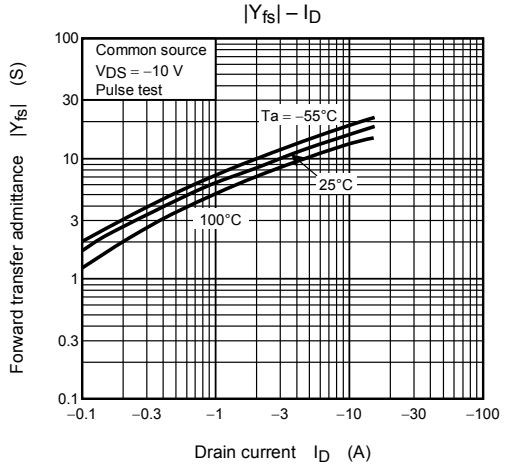
$I_D - V_{GS}$



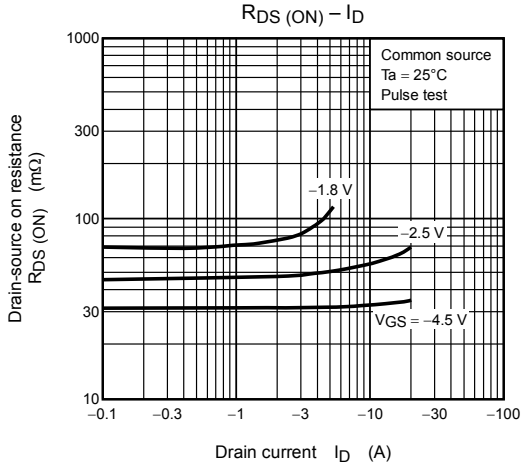
$V_{DS} - V_{GS}$



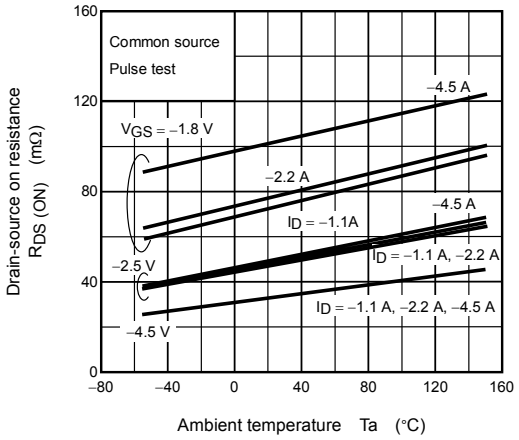
$|Y_{fs}| - I_D$



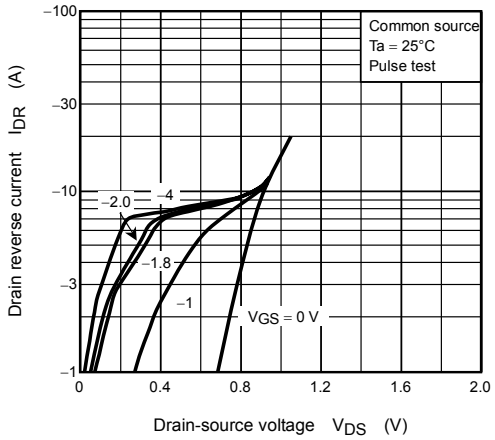
$R_{DS\ (ON)} - I_D$



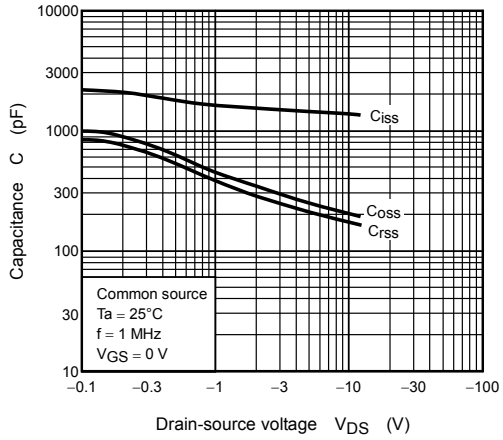
$R_{DS\ (ON)}$ – Ta



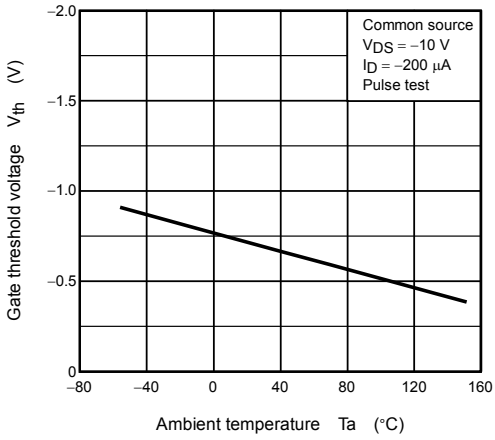
I_{DR} – V_{DS}



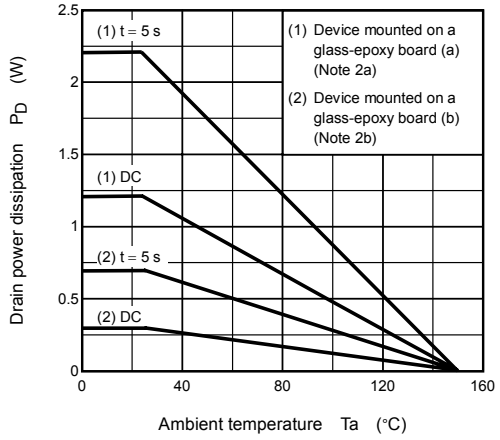
Capacitance – V_{DS}



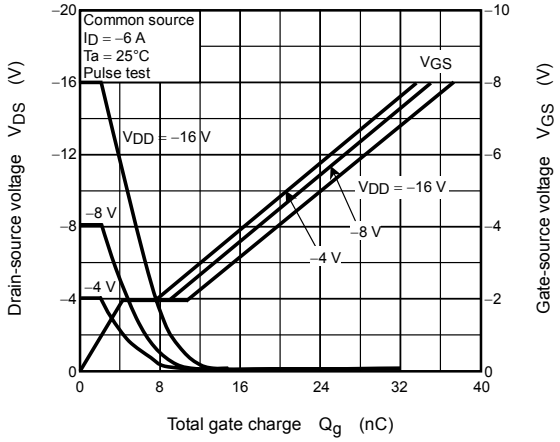
V_{th} – Ta



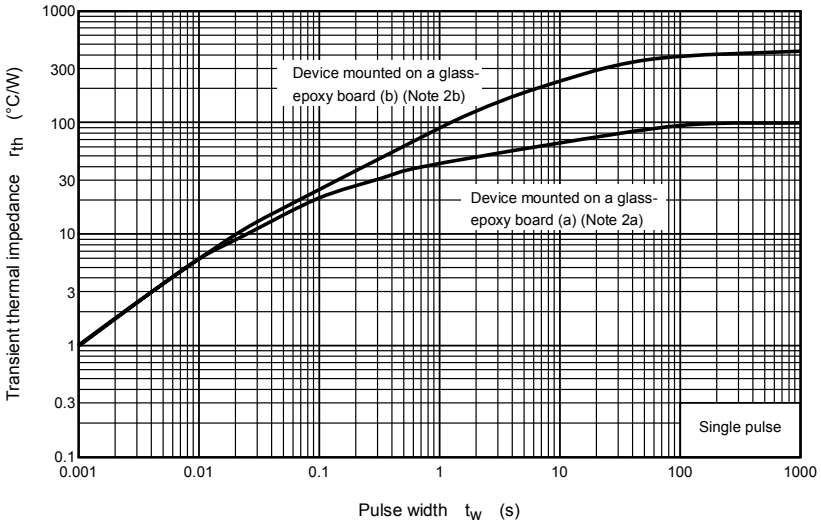
P_D – Ta



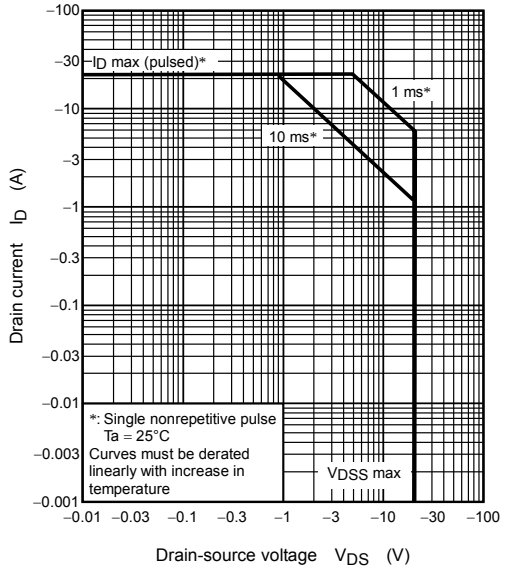
Dynamic input/output characteristics



$r_{th} - t_w$



Safe operating area



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